

IN THE CLAIMS

Kindly cancel claims 8-12 and 15-20, without prejudice, and amend claim 1 as shown in the following claim listing:

1. (currently amended) A method of manufacturing a magnetic tunnel junction device, in which a stack comprising two magnetic layers and a barrier layer extending in between is formed, one of the magnetic layers is structured by etching, in which, during etching, a part of the structured layer is thinned by removing material to provide a rest layer, whereafter the electrical resistance of the rest layer is increased by chemical conversion ~~is~~ effected by oxidation and/or nitridation.

2. (canceled)

3. (original) A method as claimed in claim 1, characterized in that physical etching is performed.

4. (original) A method as claimed in claim 1, characterized in that the magnetic layer to be structured is built up from, consecutively, a basic layer and a layer structure comprising at least a further layer for magnetic pinning of the basic layer.

5. (previously presented) A method as claimed in claim 3, characterized in that, the magnetic layer to be structured is

built up from, consecutively, a basic layer and a layer structure, and prior to physical etching, the layer structure is chemically etched until the basic layer is reached.

6. (previously presented) A method as claimed in claim 1, characterized in that an oxidation of the rest layer is effected by thermal oxidation, plasma oxidation or UV-assisted oxidation.

7. (previously presented) A method as claimed in claim 1, characterized in that a nitridation of the rest layer is effected by thermal nitridation or plasma nitridation.

8. (canceled)

9. (canceled)

10. (canceled)

11. (canceled)

12. (canceled)

13. (previously presented) A method as claimed in claim 4, characterized in that, prior to physical etching, the layer structure is chemically etched until the basic layer is reached.

14. (canceled)

15. (canceled)

16. (canceled)

17. (canceled)

18. (canceled)

19. (canceled)

20. (canceled)